



Product Summary

V _{(BR)DSS}	R _{DS(on)TYP}	I _D
-20V	400mΩ@-4.5V	-0.66A
	570mΩ@-2.5V	
	810mΩ@-1.8V	

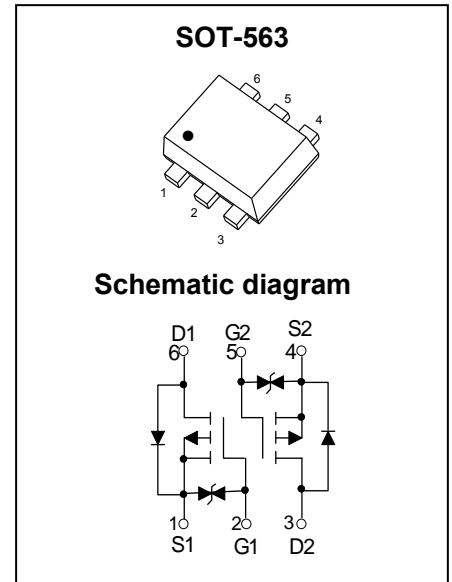
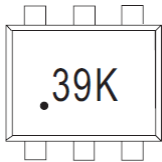
Feature

- Trench Technology Power MOSFET
- Low R_{DS(ON)}
- Low Gate Charge
- ESD Protected

Application

- Load Switching
- Low Current Inverters
- Low Current DC/DC Converters

MARKING:



ABSOLUTE MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain - Source Voltage	V _{DS}	-20	V
Gate - Source Voltage	V _{GS}	±12	V
Continuous Drain Current ^{1,5}	I _D	-0.66	A
Pulsed Drain Current ²	I _{DM}	-2.0	A
Power Dissipation ^{4,5}	P _D	0.25	W
Thermal Resistance from Junction to Ambient ⁵	R _{θJA}	500	°C/W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{STG}	-55~ +150	°C

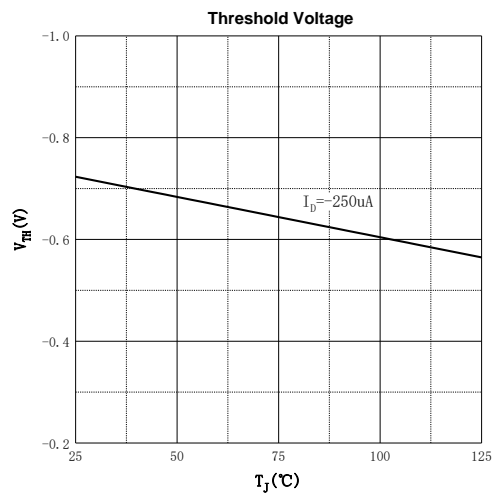
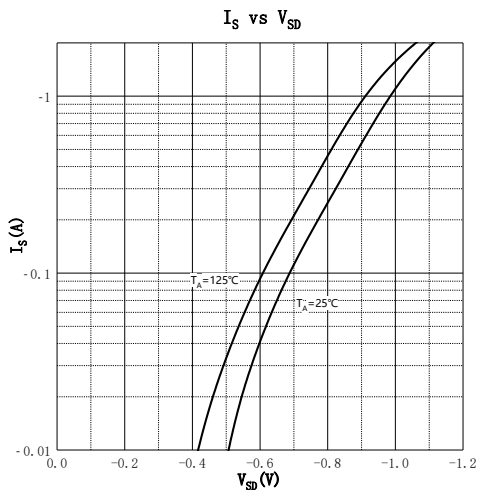
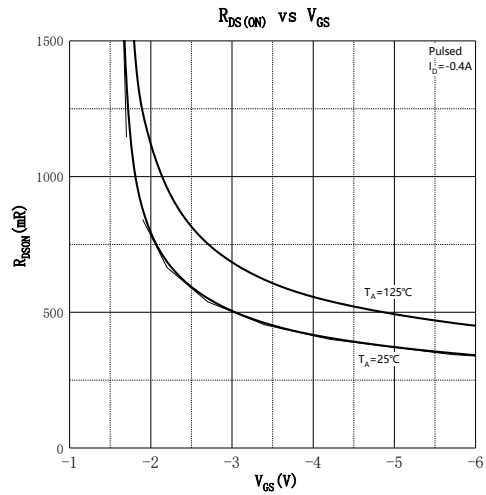
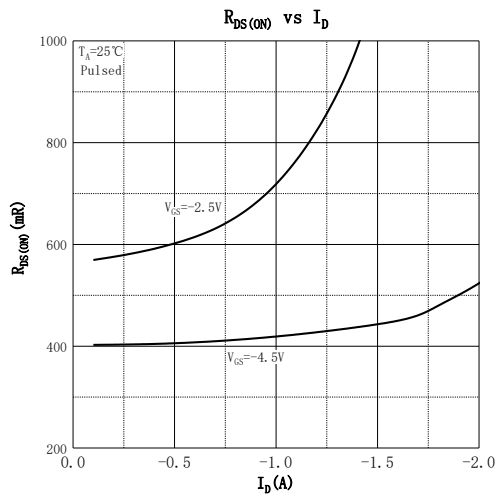
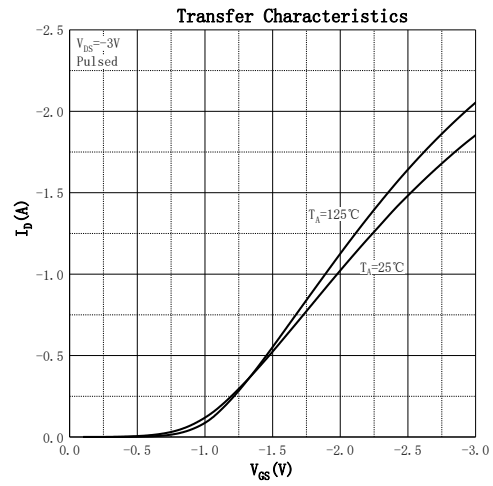
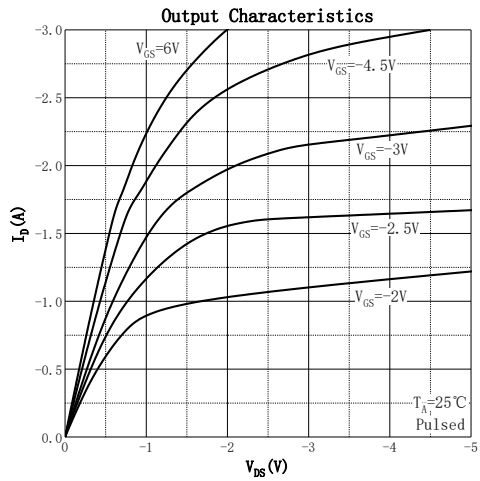
MOSFET ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain - Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-20			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -16V, V_{GS} = 0V$			-1	μA
Gate - Body Leakage Current	I_{GSS}	$V_{GS} = \pm 10V, V_{DS} = 0V$			± 10	μA
On Characteristics³						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-0.4	-0.7	-1.0	V
Drain-source On-resistance	$R_{DS(on)}$	$V_{GS} = -4.5V, I_D = -0.5A$		400	520	m Ω
		$V_{GS} = -2.5V, I_D = -0.3A$		570	780	
		$V_{GS} = -1.8V, I_D = -0.12A$		810	1100	
Forward Transconductance	g_{FS}	$V_{DS} = -5V, I_D = -0.4A$		1		S
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS} = -10V, V_{GS} = 0V, f = 1MHz$		79		pF
Output Capacitance	C_{oss}			15		
Reverse Transfer Capacitance	C_{rss}			13		
Switching Characteristics						
Total Gate Charge	Q_g	$V_{DS} = -10V, V_{GS} = -4.5V, I_D = -0.2A$		2.26		nC
Gate-source Charge	Q_{gs}			0.45		
Gate-drain Charge	Q_{gd}			0.24		
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = -10V, V_{GS} = -4.5V,$ $R_L = 50\Omega, R_G = 3\Omega$		8		ns
Turn-on Rise Time	t_r			5.5		
Turn-off Delay Time	$t_{d(off)}$			30		
Turn-off Fall Time	t_f			17		
Source - Drain Diode Characteristics						
Diode Forward Voltage ³	V_{SD}	$V_{GS} = 0V, I_S = -0.5A$			1.2	V

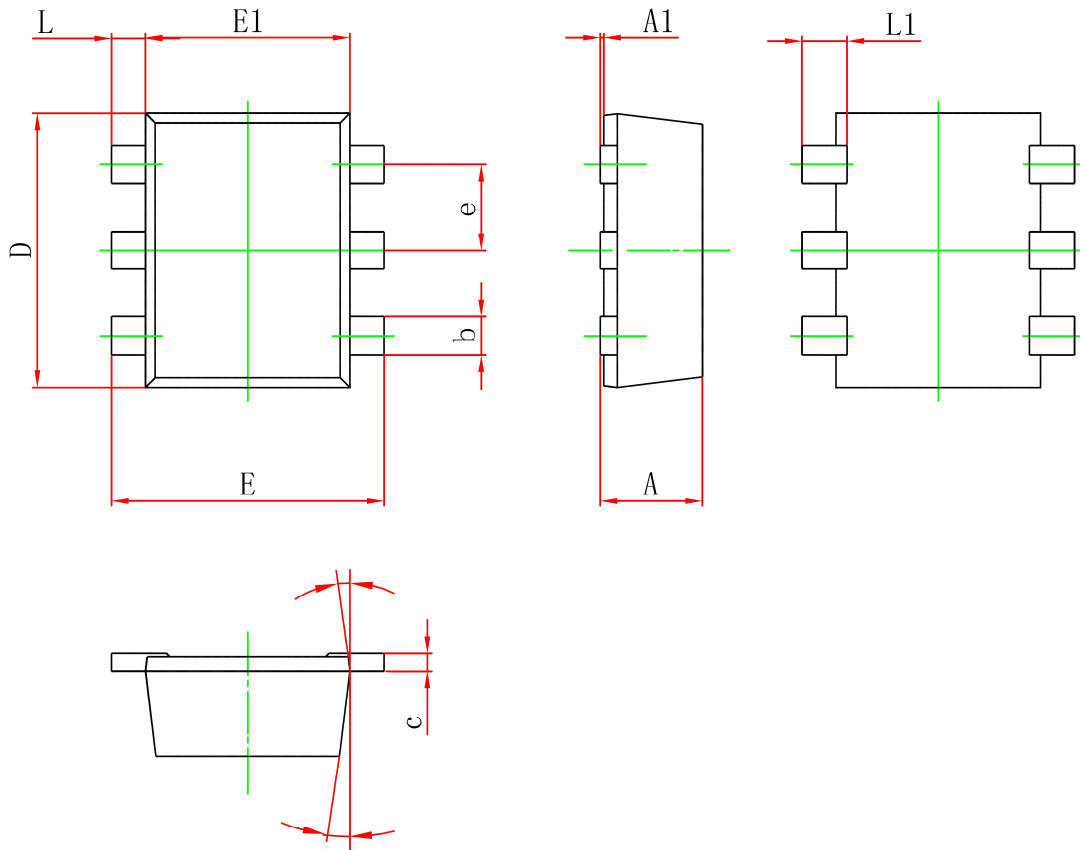
Notes :

- 1.The maximum current rating is limited by package.
- 2.Repetitive rating:pulse width limited by $T_{J(MAX)} = 150^\circ\text{C}$.
- 3.Pulse Test : Pulse Width $\leq 300\mu s$, duty cycle $\leq 2\%$.
- 4.The power dissipation P_D is limited by $T_{J(MAX)} = 150^\circ\text{C}$.
- 5.Device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$.

Typical Characteristics



SOT-563 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.500	0.600	0.020	0.024
A1	0.000	0.050	0.000	0.002
e	0.450	0.550	0.018	0.022
c	0.080	0.180	0.003	0.007
D	1.500	1.700	0.059	0.067
b	0.170	0.270	0.007	0.011
E1	1.100	1.300	0.043	0.051
E	1.500	1.700	0.059	0.067
L	0.100	0.300	0.004	0.012
L1	0.200	0.400	0.008	0.016
θ	7°		7°	